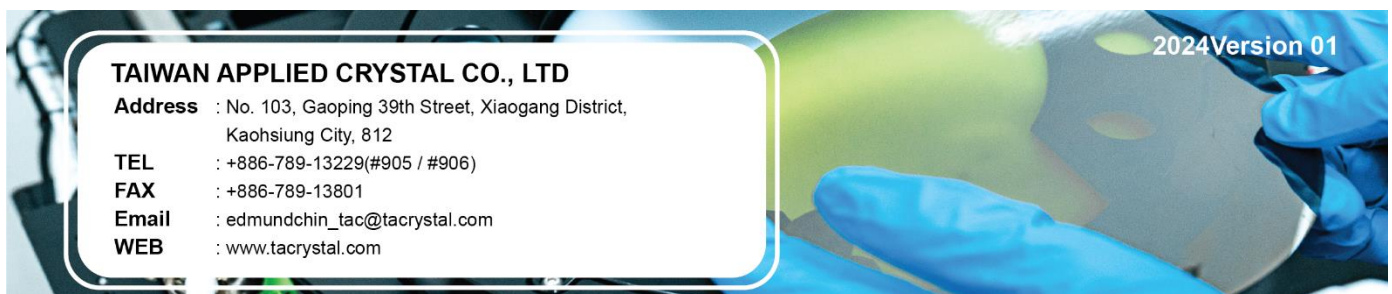


TAC 8" SiC 4H N-Type Specification

Grade	Dummy	Prime
Diameter	199.5-200.0 mm	199.5-200.0 mm
Polytype	4H	4H
Thickness	500 $\mu\text{m} \pm 25 \mu\text{m}$	500 $\mu\text{m} \pm 25 \mu\text{m}$
Wafer Orientation	4° toward <11-20> $\pm 0.5^\circ$	4° toward <11-20> $\pm 0.5^\circ$
MP	$\leq 15/\text{cm}^2$	$\leq 0.2/\text{cm}^2$
Resistivity	0.015-0.028 ohm · cm	0.015-0.025 ohm · cm
LTV	10 μm	5 μm
TTV	15 μm	10 μm
Bow	50 μm	35 μm
Warp	100 μm	70 μm
BPD	N/A	< 1000 /cm ²
TSD	N/A	< 50 /cm ²
TED	N/A	< 4000 /cm ²
EPD	N/A	< 5000 /cm ²
Roughness (Polish/CMP)	Ra<1 nm/Ra<0.5 nm	Ra<1 nm/Ra<0.2 nm
Si-face scratches (Cumulative length)	<200 mm	none
Packaging	Multi-wafer cassette or single wafer container (vacuum, no air leakage & damage)	:Multi-wafer cassette or single wafer container (vacuum, no air leakage & damage)



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